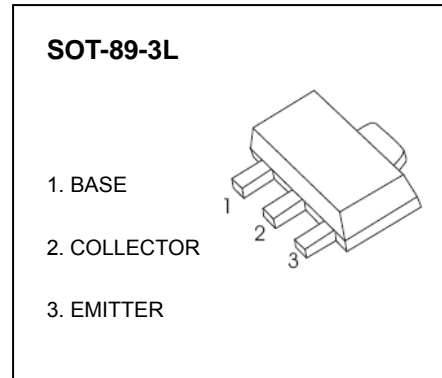


SOT-89-3L Plastic-Encapsulate Transistors

KTA1666 TRANSISTOR (PNP)

FEATURES

- Complementary to KTC4379
- Small Flat Package
- Low Saturation Voltage
- Power Amplifier and Switching Application



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-2	A
P _C	Collector Power Dissipation	500	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	250	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -1mA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-1mA, I _C =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} =-50V, I _E =0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-100	nA
DC current gain	h _{FE(1)} *	V _{CE} =-2V, I _C =-500mA	70		240	
	h _{FE(2)} *	V _{CE} =-2V, I _C =-1.5A	40			
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =-1A, I _B =-50mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =-1A, I _B =-50mA			-1.2	V
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			40	pF
Transition frequency	f _T	V _{CE} =-2V, I _C = -500mA		120		MHz

*Pulse test: pulse width ≤300mS, duty cycle≤ 2.0%.

CLASSIFICATION OF h_{FE(1)}

RANK	O	Y
RANGE	70 - 140	120 - 240
MARKING	WO	WY

Typical Characteristics

KTA1666

